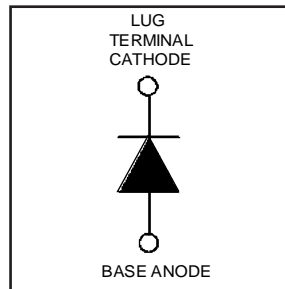


HFA90NH40R

Ultrafast, Soft Recovery Diode

Features

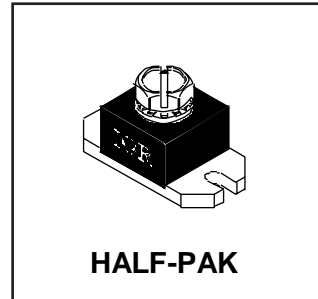
- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters



$V_R = 400V$
$V_{F(typ.)}^{③} = 1V$
$I_{F(AV)} = 90A$
$Q_{rr} (typ.) = 420nC$
$I_{RRM}(typ.) = 9.3A$
$t_{rr}(typ.) = 36ns$
$di_{(rec)}/dt (typ.)^{③} = 260A/\mu s$

Description

HEXFRED™ diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.



Absolute Maximum Ratings (per Leg)

	Parameter	Max.	Units
V_R	Cathode-to-Anode Voltage	400	V
$I_F @ T_C = 25^\circ C$	Continuous Forward Current	148	A
$I_F @ T_C = 100^\circ C$	Continuous Forward Current	72	
I_{FSM}	Single Pulse Forward Current ①	600	
E_{AS}	Non-Repetitive Avalanche Energy ②	1.4	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	260	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	104	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

Thermal - Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
R_{thJC}	Junction-to-Case	—	—	0.48	°C/W
R_{thCS}	Case-to-Sink, Flat, Greased Surface	—	0.15	—	K/W
Wt	Weight	—	26 (0.9)	—	g (oz)
	Mounting Torque ④	15 (1.7)	—	25 (2.8)	lbf•in
	Terminal Torque	30 (3.4)	—	40 (4.6)	(N•m)
	Vertical Pull	—	—	80	lbf•in
	2 inch Lever Pull	—	—	40	

Note: ① Limited by junction temperature
 ② $L = 100\mu H$, duty cycle limited by max T_J
 ③ $125^\circ C$

④ Mounting surface must be smooth, flat, free of burrs or other protrusions. Apply a thin even film of thermal grease to mounting surface. Gradually tighten each mounting bolt in 5-10 lbf•in steps until desired or maximum torque limits are reached. Module

HFA90NH40R

PD-2.469 rev. B 02/99

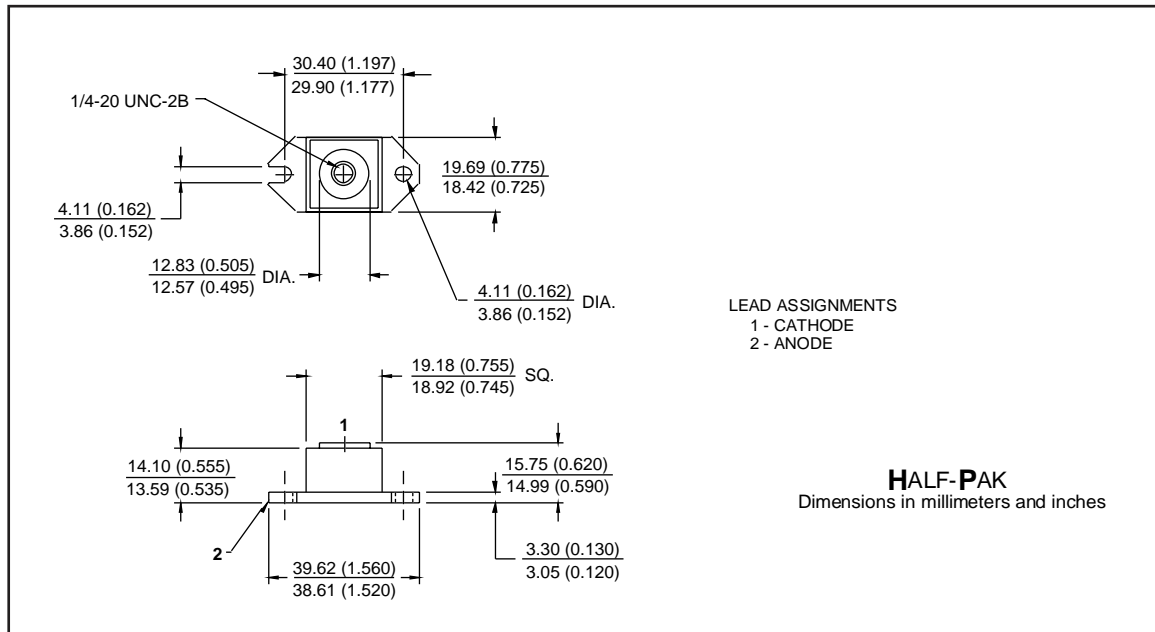
International
IOR Rectifier

Electrical Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions
V_{BR} Cathode Anode Breakdown Voltage	400	—	—	V	$I_R = 100\mu\text{A}$
V_{FM} Max Forward Voltage See Fig. 1	—	1.1	1.3	V	$I_F = 90\text{A}$
	—	1.3	1.5		$I_F = 180\text{A}$
	—	1.0	1.2		$I_F = 90\text{A}, T_J = 125^\circ\text{C}$
I_{RM} Max Reverse Leakage Current See Fig. 2	—	1.0	6.0	μA	$V_R = V_R \text{ Rated}$
	—	1.5	8.0	mA	$T_J = 125^\circ\text{C}, V_R = 400\text{V}$
C_T Junction Capacitance See Fig. 3	—	180	260	pF	$V_R = 200\text{V}$
L_S Series Inductance	—	7.0	—	nH	From top of terminal hole to mounting plane

Dynamic Recovery Characteristics (per Leg) @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions	
t_{rr} Reverse Recovery Time See Fig. 5	—	36	—	ns	$I_F = 1.0\text{A}, di_f/dt = 200\text{A}/\mu\text{s}, V_R = 30\text{V}$ $T_J = 25^\circ\text{C}$	
t_{rr1}	—	90	140			$T_J = 125^\circ\text{C}$
t_{rr2}	—	160	240			$T_J = 125^\circ\text{C}$
I_{RRM1} Peak Recovery Current See Fig. 6	—	9.3	17	A	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	
I_{RRM2}	—	15	30			$T_J = 125^\circ\text{C}$
Q_{rr1} Reverse Recovery Charge See Fig. 7	—	420	1100	nC	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	
Q_{rr2}	—	1200	3200			$T_J = 125^\circ\text{C}$
$di_{(rec)M}/dt1$ Peak Rate of Fall of Recovery Current $di_{(rec)M}/dt2$ During t_b See Fig. 8	—	360	—	A/ μs	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	
	—	260	—			



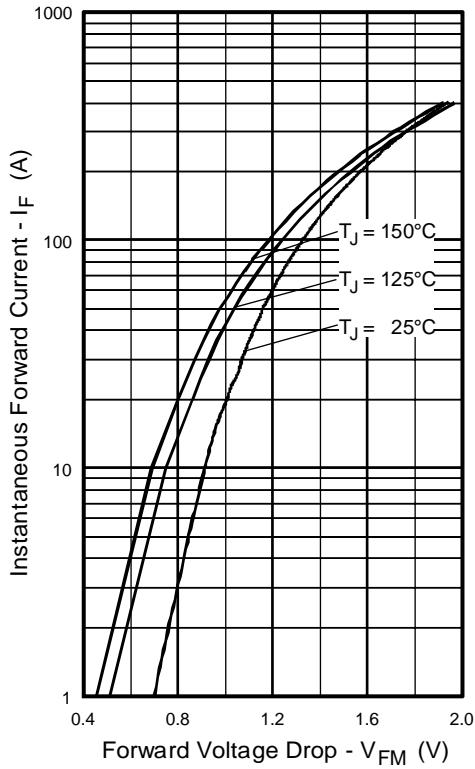


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

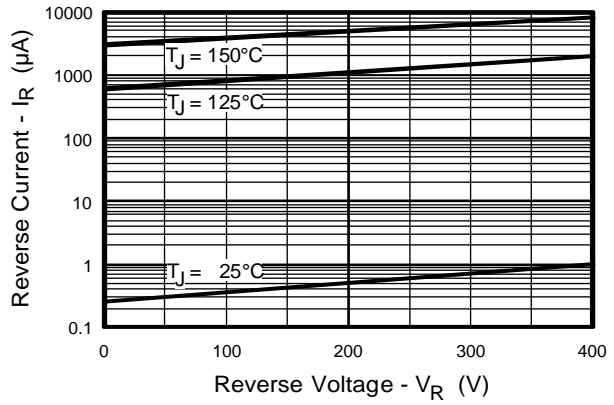


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

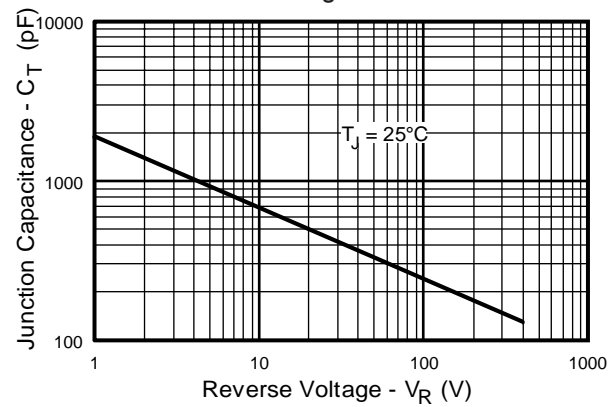


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

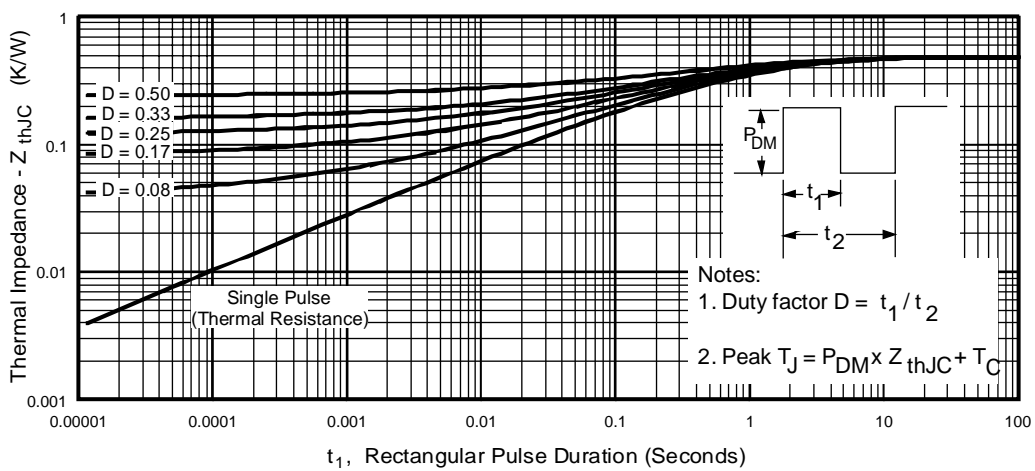


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

HFA90NH40R

PD-2.469 rev. B 02/99

International
IOR Rectifier

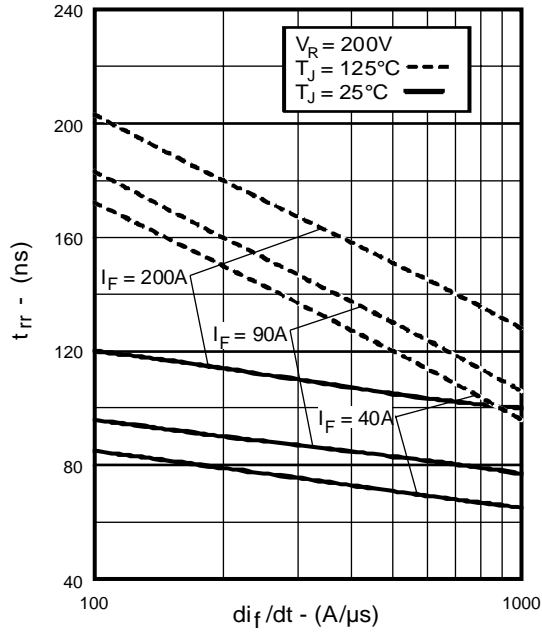


Fig. 5 - Typical Reverse Recovery vs. di_f/dt

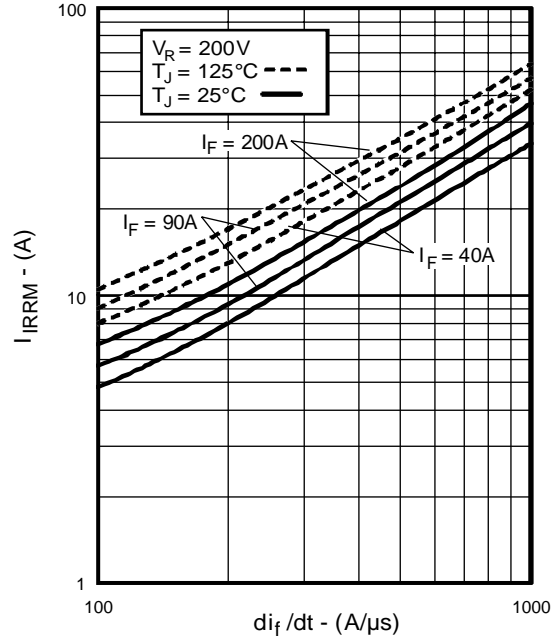


Fig. 6 - Typical Recovery Current vs. di_f/dt

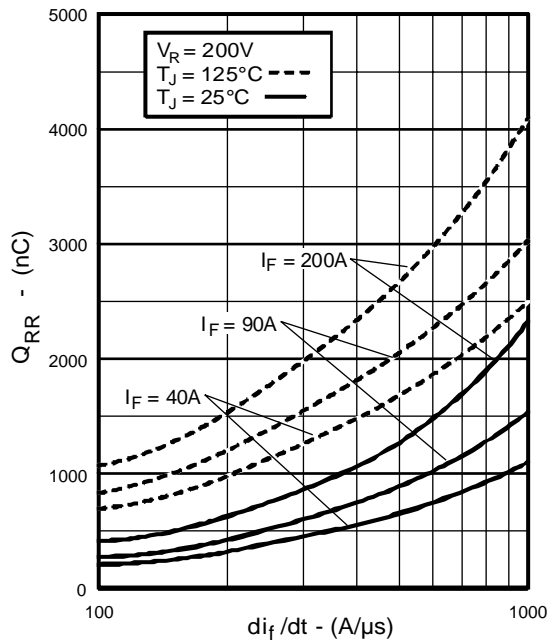


Fig. 7 - Typical Stored Charge vs. di_f/dt

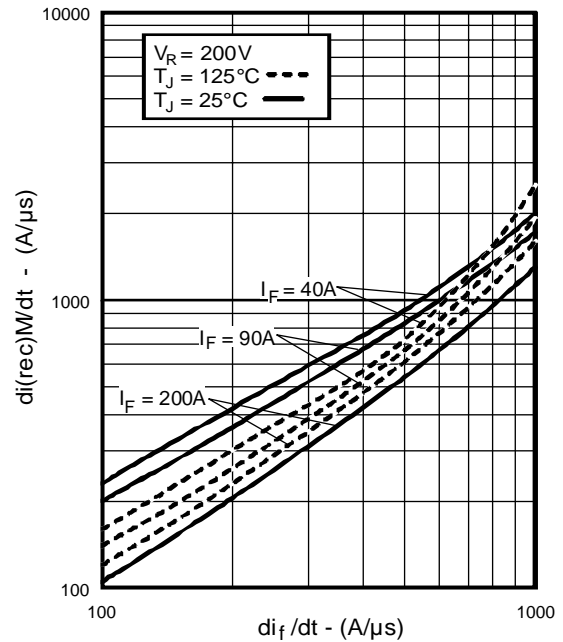


Fig. 8 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

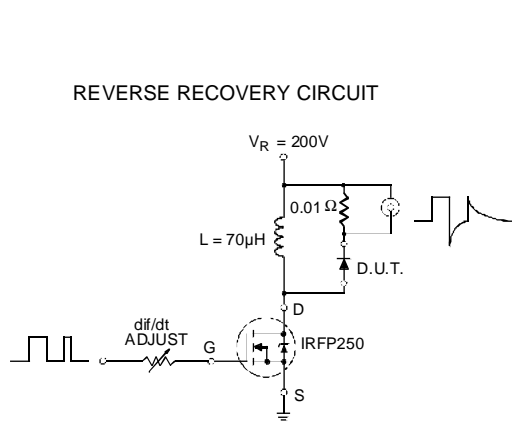


Fig. 9 - Reverse Recovery Parameter Test Circuit

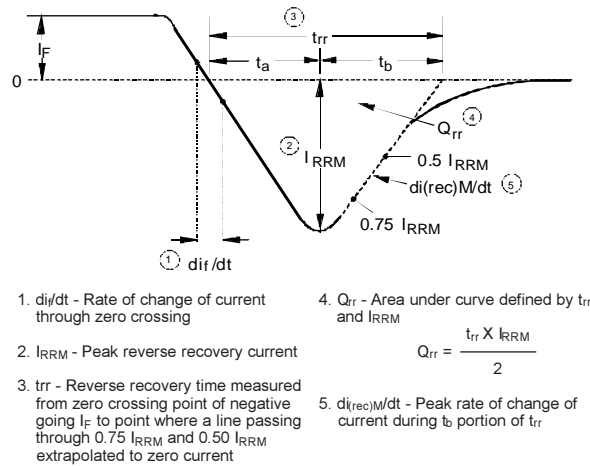


Fig. 10 - Reverse Recovery Waveform and Definitions

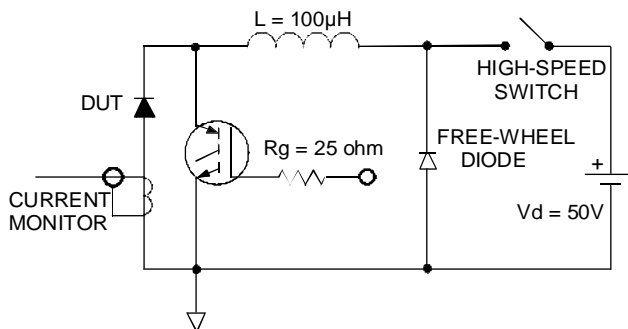


Fig. 11 - Avalanche Test Circuit and Waveforms

WORLDHEADQUARTERS: 233 Kansas St., El Segundo, California 90245 U.S.A. Tel: (310) 322 3331. Fax: (310) 322 3332.
EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, U.K. Tel: ++ 44 1883 732020. Fax: ++ 44 1883 733408.
IR CANADA: 15 Lincoln Court, Brampton, Markham, Ontario L6T3Z2. Tel: (905) 453 2200. Fax: (905) 475 8801.
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg. Tel: ++ 49 6172 96590. Fax: ++ 49 6172 965933.
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino. Tel: ++ 39 11 4510111. Fax: ++ 39 11 4510220.
IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo, Japan 171. Tel: 81 3 3983 0086.
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994. Tel: ++ 65 838 4630.
IR TAIWAN: 16 Fl. Suite D.207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan. Tel: 886 2 2377 9936.